[CLAIMS]

[claim 1]

A method for cleaning a silicon wafer after mirror-polishing which comprises the steps of:

cleaning the silicon wafer with an SC1 cleaning solution,

cleaning the silicon wafer cleaned by the SC1 cleaning solution with hydrofluoric acid, and

cleaning the silicon wafer cleaned by the hydrofluoric acid with ozonated water having an ozone concentration of 3 ppm or more,

wherein an etching removal of the silicon wafer with the SC1 cleaning solution is made 0.1 to 2.0 nm.

~~[claim 2]~~

~~The method for cleaning a silicon wafer according to claim 1, wherein surface roughness Rms of the cleaned silicon wafer is 0.1 nm or less.~~